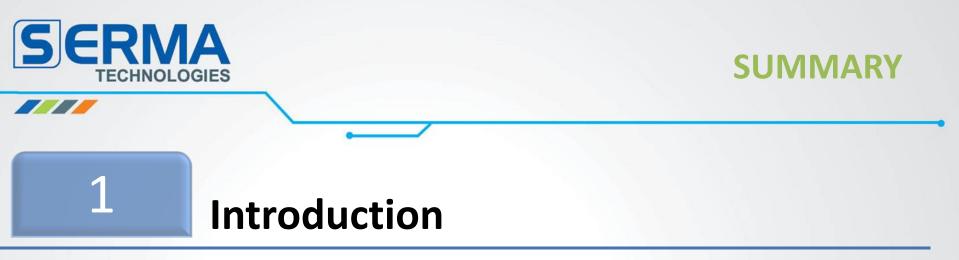


Passive Components Networking Symposium 15-17 September 2017 – Brno, Czech Republic



Failure Analysis feedback From all markets

Eric ZAIA (Technical coordinator - Passive components and PCBA) Béatrice MOREAU (Passive components & PCB Expert)



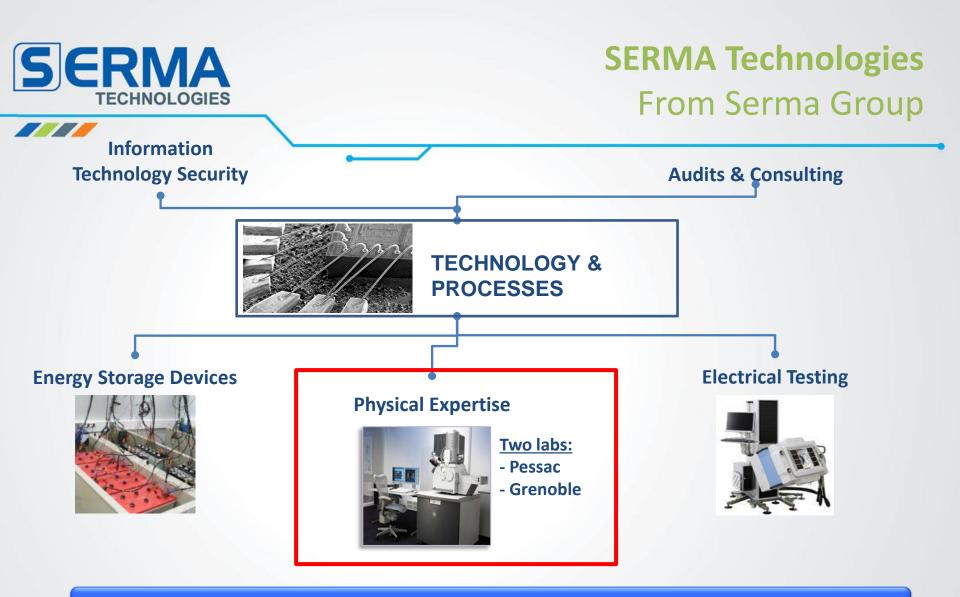
SERMA Technologies

Serma's Figures on Failure Analysis (FA)

- Statistics about Passive FA
- Main defects observed on Passive Components
 - Capacitors (Ceramic, Tantalum)
 - Resistors (Thick, Thin films)



1-Introduction

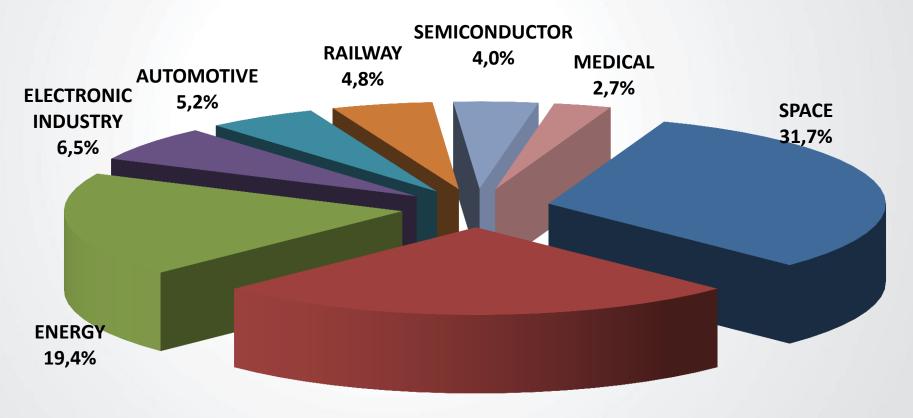


The most important independent electronic laboratory in Europe

- > 6 000 analyses / year
- > 20 years of experience multi-sectoral



Physical Expertise Main markets (by Turnover)

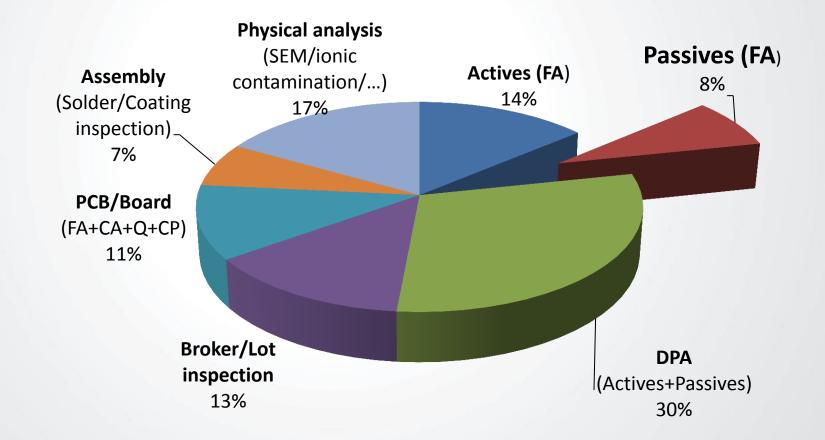


AVIONICS 25,2%



Physical Expertise Type of analysis (by quantity)

• 2011 - 2016: 23000 analyses in Serma's Lab

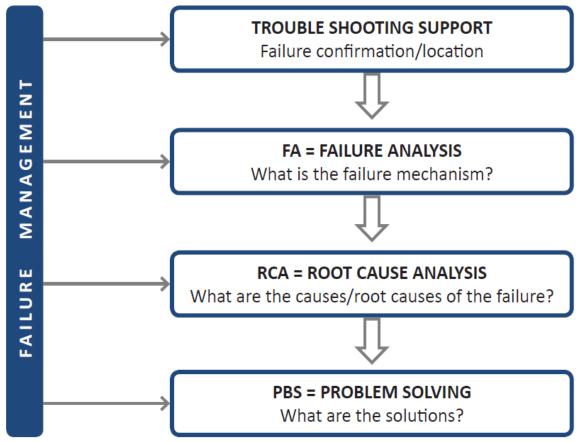




Failure Analysis Management

Serma is solicited for:

- Knowledge
- Material means
- Internal capability
- when an independent third party is needed

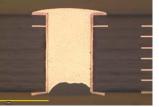




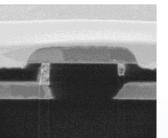
SERMA Technologies Physical expertise

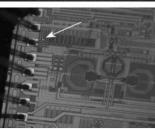
A WIDE RANGE OF TECHNIQUES

Non Destructives: Optical microscopes 2D & 3D X-Ray Electrical Tests Micro-probing X-Ray Fluorescence IR Thermography Acoustic microscopy









Destructives: Cross section Laser Cutter Chemical etch and plasma dry etch SEM with EDX system Focused ion Beam imaging 3D Slice & View Transmission Electron Microscopy



2- Serma's Figures on FA



EXPERIENCE CAPITALIZATION

2009: Creation of a Data base \rightarrow Key Words after each analysis

	nulaire			
Serma Tech	INOLOGIES	Fiche	mots clés	
Critères de reche	rche Une fois votre	critères sélectio	nnés appuyez sur F5 pour exé	cuter.
	Analyste:		Client:	
Date : 02/	07/2009		Affaire AF09	-2193
Référence : CAPA	TANTALE		Fabricant : SAMSUNG	
Expertise : FAP	assif	*	Composant : Capacité tantale	<u>.</u>
Boitier : CMS		•	Technologie :	•
MODES de DEFA		Défaut ASSEMBLAG	E I	
Défaillance 2 : Fis		_	Défaillance 3 :	
CARACTERISTIC	UES PCB		1	
Finition :		v	Nature PCB :	
Stade étude :		•		
PROCEDE D'ASS	EMBLAGE et ALLIAGE U	JTILISE		

reference_fich -				boitier_fiche-	mode_def_1_fiche -	
TMS15A03	XXXX	FA Passif	SERTISSAGE			Aucun
	XXXX	FA Passif	Capacité céramique	CMS		Fissuration
	XXXX	FA Passif	Fitre	Axial	/Stress/Vieilissement	
	XXXX	FA Passif	Thermistance		Défaut ASSEMBLAGE	Soudure(rupture joint)
G1675588	XXXX	FA Passif	Transformateur		Défaut COMPOSANT	Fissuration
	XXXX	FA Passif	Capacité céramique	CMS		CONTRAINTE Thermomécani
SN6278/SN5965	XXXX	FA Passif	Relais / Switch	Axial		Pb mécanique
8,25nF	XXXX	FA Passif	Autre	Radial		Aucun
SN000036/SN000007	XXXX	FA Passif	Relais / Switch	Axial	Défaut ASSEMBLAGE	Contamination
EM	XXXX	FA Passif	Capteur divers	Module Complet	Défaut COMPOSANT	Autre
	XXXX	FA Passif	Capacité film			Effet corona
	XXXX	FA Passif	Fusible	CMS	Défaut COMPOSANT	Fissuration
	XXXX	FA Passif	Capteur divers	Module Complet		Autre
	XXXX	FA Passif	Relais	Module Complet	/Stress/Vieilissement	Dégradation contacts
JDC-20-J	XXXX	FA Passif		SO	Défaut COMPOSANT	Rupture fil de liaison
PT1000	XXXX	FA Passif	Capteur divers	TO/SOT	Défaut COMPOSANT	Autre
DS2E-F-DC12V	XXXX	FA Passif	Relais	DIL	/Stress/Vieilissement	Contamination
FBAC012	XXXX	FA Passif	Capacité céramique	РТН	Défaut ASSEMBLAGE	Fonte joint brasé
DS4E-S-DC24V	XXXX	FA Passif	Relais			Autre
RAL-24W-K	XXXX	FA Passif	Relais			Autre
XXX	XXXX	FA Passif	Capacité céramique	CMS		Contrainte mécanique
XXX	XXXX	FA Passif	Capacité céramique	CMS		Fissuration
	XXXX	FA Passif	Capacité film		EOS/ESD	Diélectrique
Module Hyper	XXXX	FA Passif				
	XXXX	FA Passif	Potentiométre		/Stress/Vieilissement	Fissuration
	XXXX	FA Passif	Potentiométre		Défaut ASSEMBLAGE	Fissuration
	XXXX	FA Passif	Transformateur		Défaut COMPOSANT	Autre
	XXXX	FA Passif	Résistance	Axial	Défaut COMPOSANT	Corrosion
	XXXX	FA Passif	Multiplexeur		Défaut COMPOSANT	Rupture fil de liaison
DS4E-S-DC24V	XXXX	FA Passif	Relais			Pollution (résidus)
RA4-24W-K	XXXX	FA Passif	Relais			Pollution (résidus)
QEN79	XXXX	FA Passif	Oscilateur	CMS		Fissuration
RESISTANCE	XXXX	FA Passif	Résistance	СМS	EOS/ESD	Fissuration
B82422H	XXXX	FA Passif				

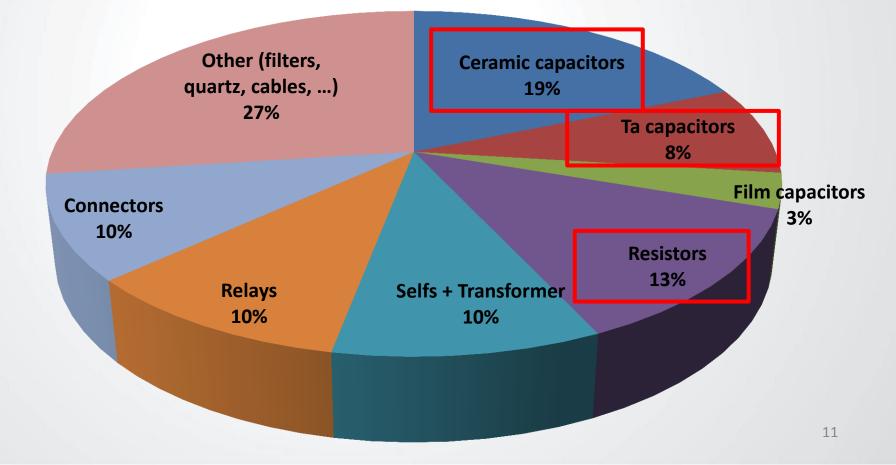
10



FAILURE ANALYSES

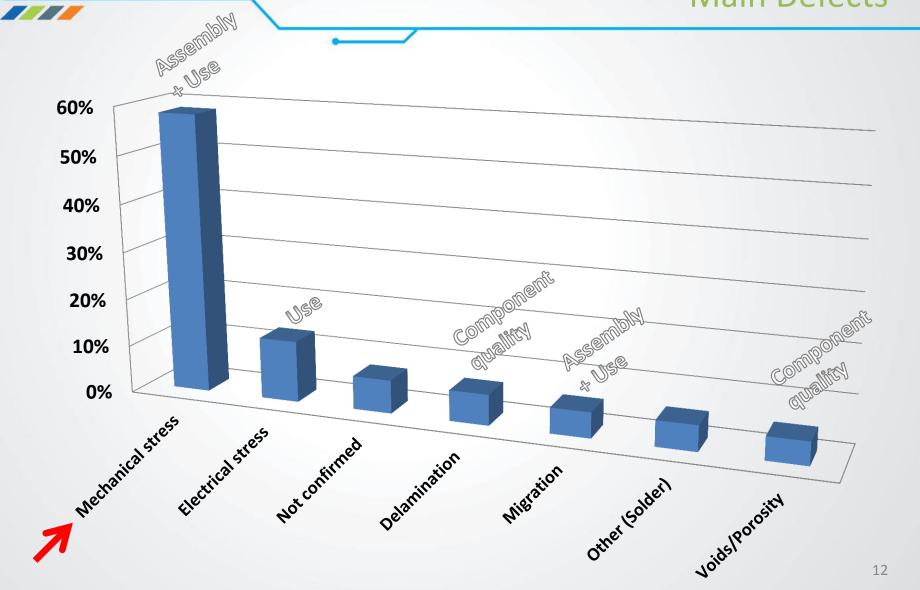
Type of component (by quantity)

• 2011 - 2016: 1 400 failure analyses on passive components



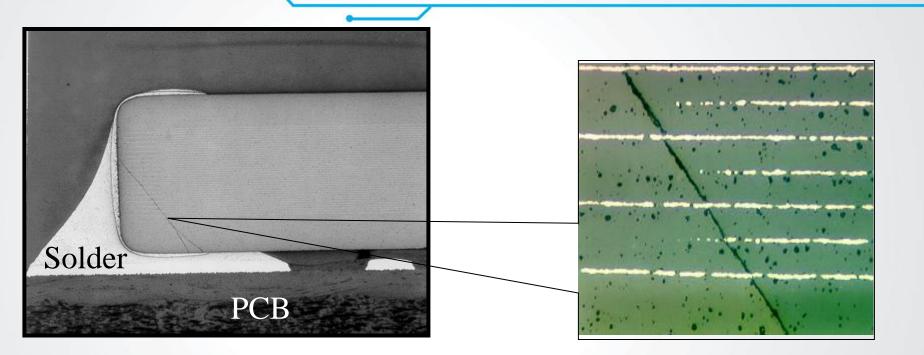


Ceramic Capacitors Main Defects





Ceramic Capacitors Cracks



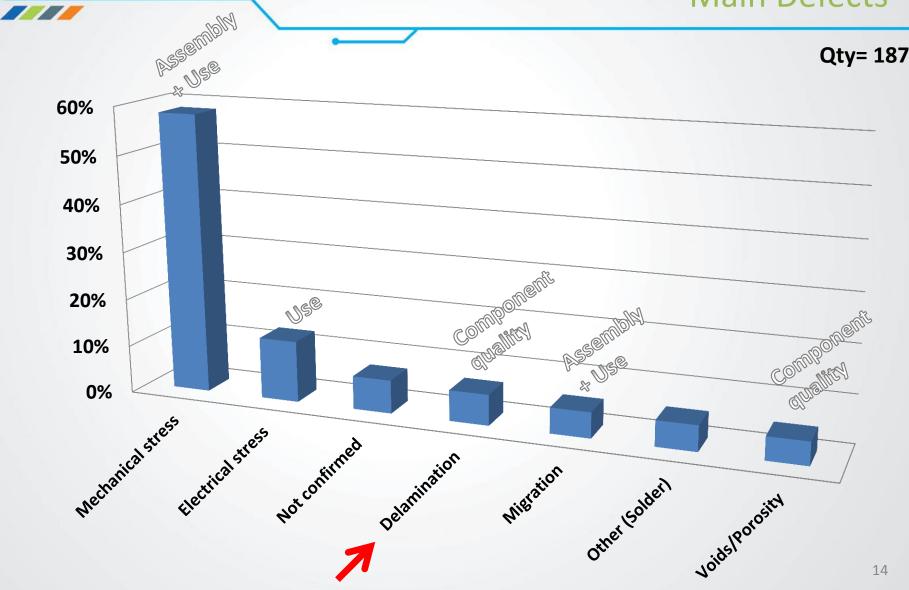
Diagonal cracks (@45°) due to Thermo and/or Mechanical stresses caused by soldering/testing/depanelization/handling...

→ Short circuit occurs when dielectric between opposite electrodes is cracked



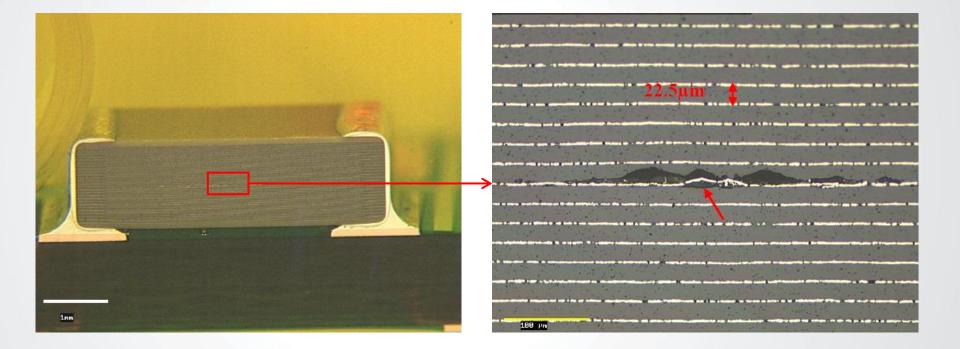
Ceramic Capacitors Main Defects







Ceramic Capacitors Delamination: Electrode/Ceramic

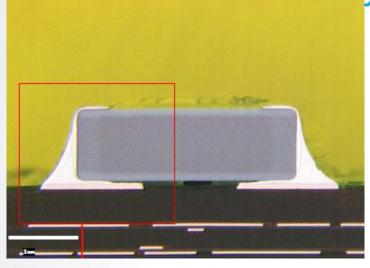


→ Results in insulation reduction up to Short circuit

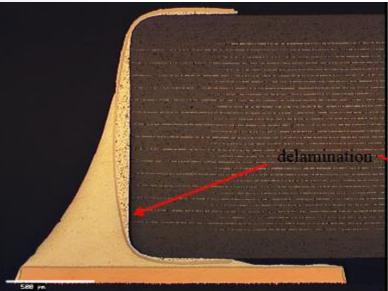


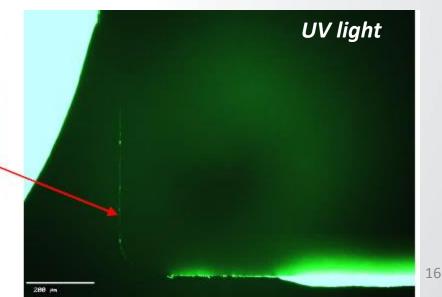
Ceramic Capacitors

Delamination Electrodes/Termination



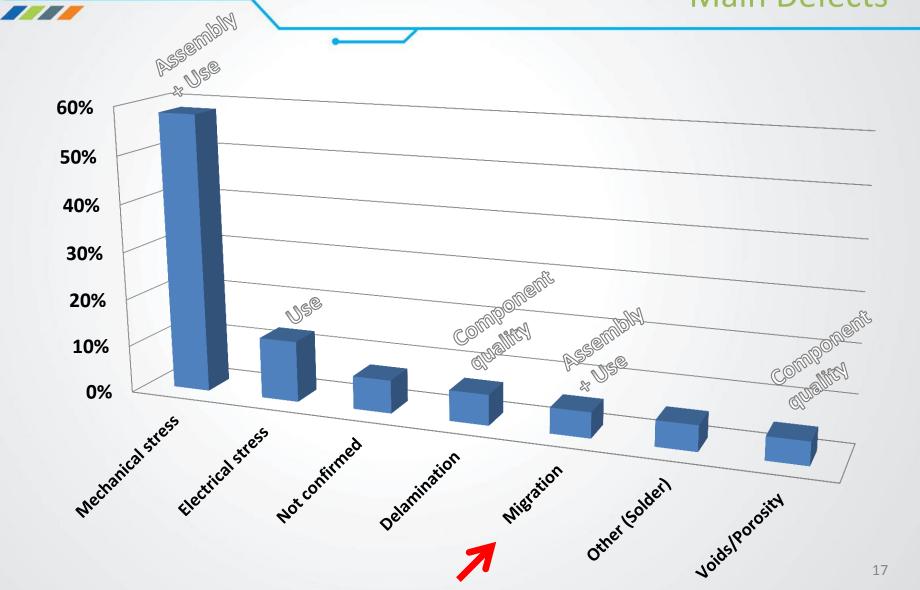
Soldering process + Component Weakness (at termination) Revealed after ageing test →results in loss of capacitance up to Open circuit





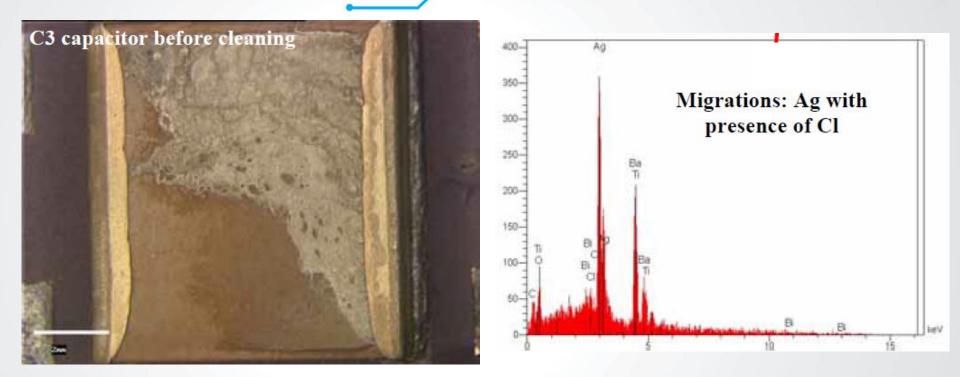


Ceramic Capacitors Main Defects





Ceramic Capacitors Migration



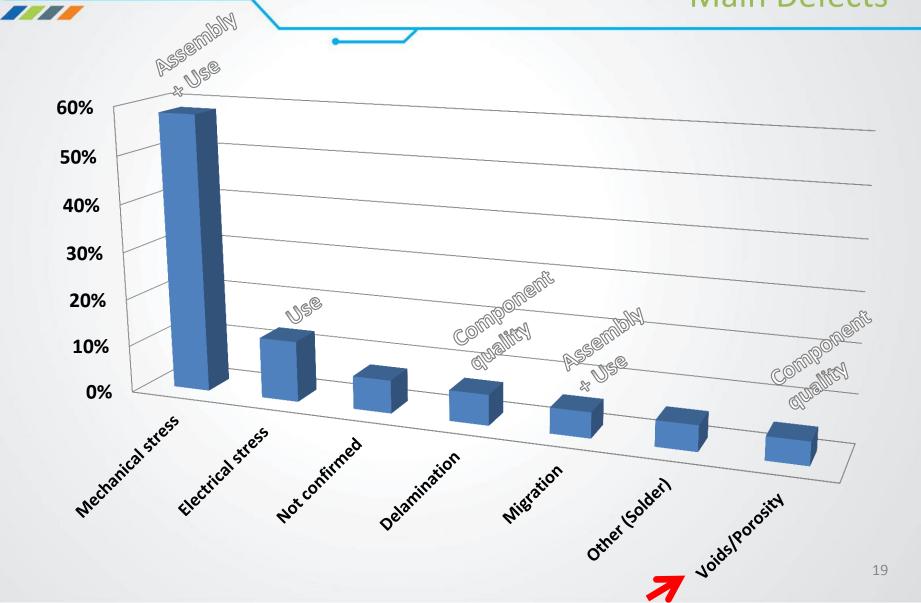
Failure occurred during Environmental tests:

Moisture and contaminant (Cl,..) leading to Silver dendritic growth

→ Short circuit

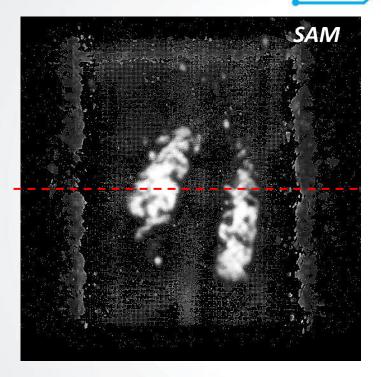


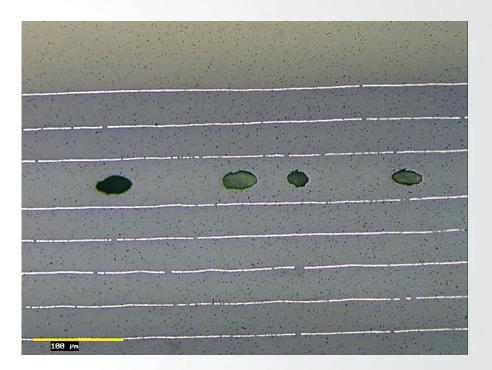
Ceramic Capacitors Main Defects





Ceramic Capacitors Porosity





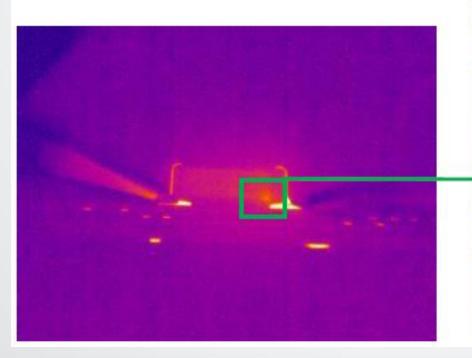
- Component quality
- Ceramic preparation issue or organic/inorganic contamination
- → Insulation reduction up to short circuit

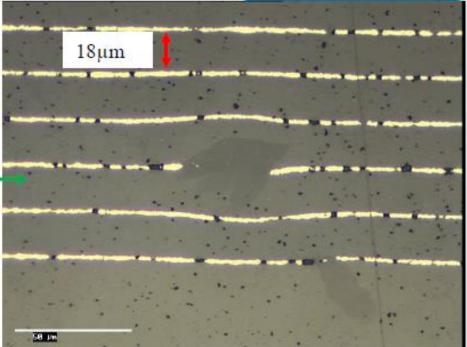


Particular Technique

Voltage contrast coupled SEM

- Presence of a short circuit on a ceramic capacitor,
- Infra red thermography confirmed the presence of the Short
- Cross section showed the presence of specific phases
- \rightarrow Conductive or not?







Classical SEM view (Chemical contrast)

O: 11,7%W Ti: 29.4%W Ba: 59.9%W

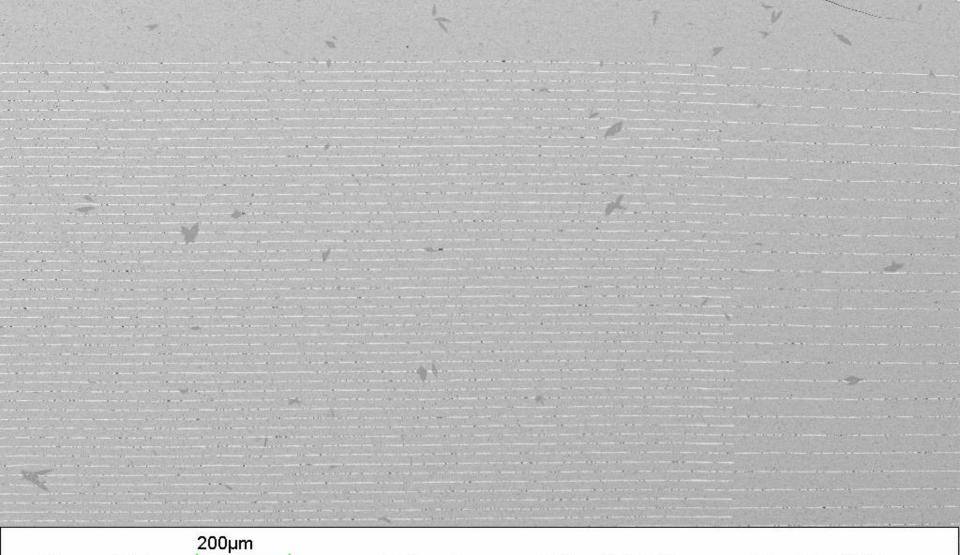
Meg = 1.02 K X

WD = 12 mm EHT

EHT = 20.00 kV

Signal A = RBSD

Classical SEM view (Chemical contrast)



Mag = 55 X

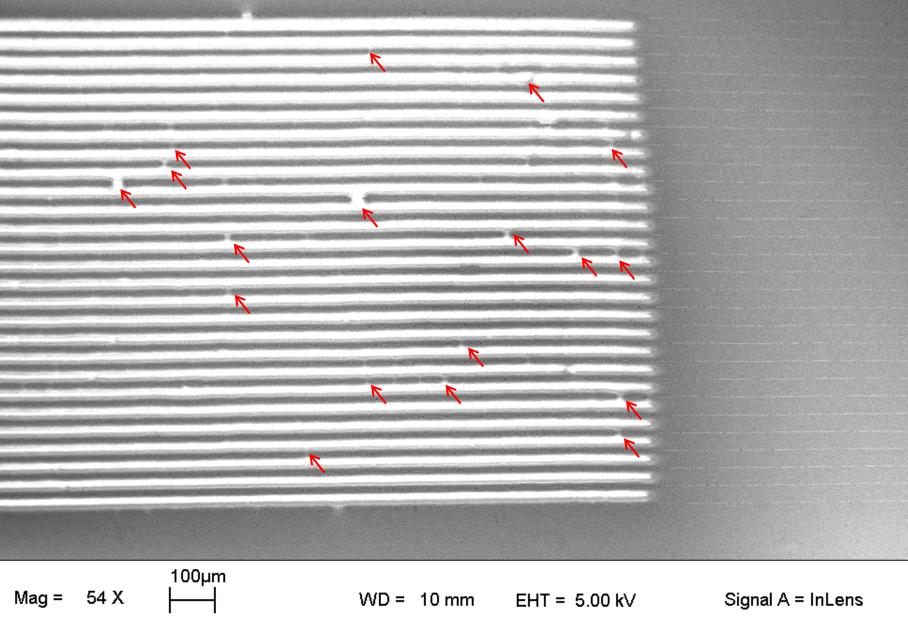


WD = 13 mm

EHT = 20.00 kV

Signal A = RBSD

SEM view (Voltage contrast)



SEM view (Voltage contrast)

100

1.1.1.1.1.1

Mag = 338 X

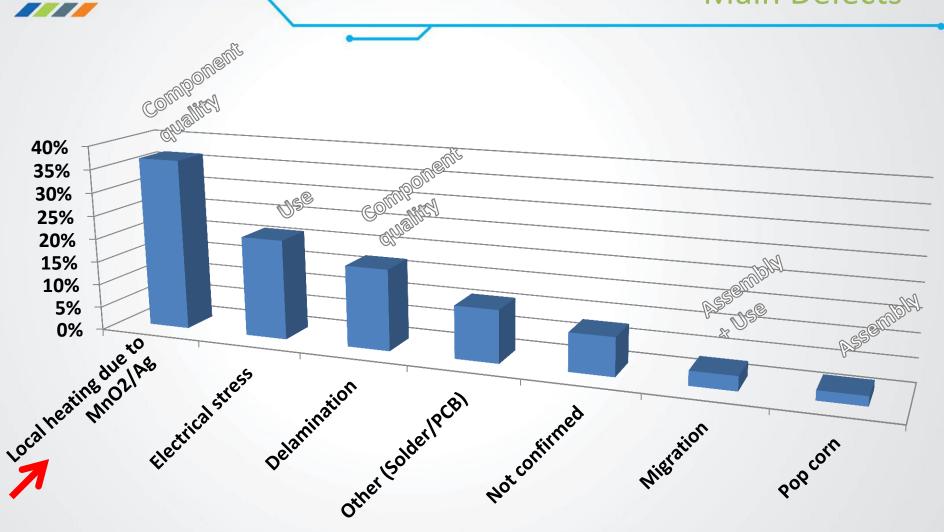
20µm

WD = 10 mm EHT = 5.00 kV

Signal A = InLens

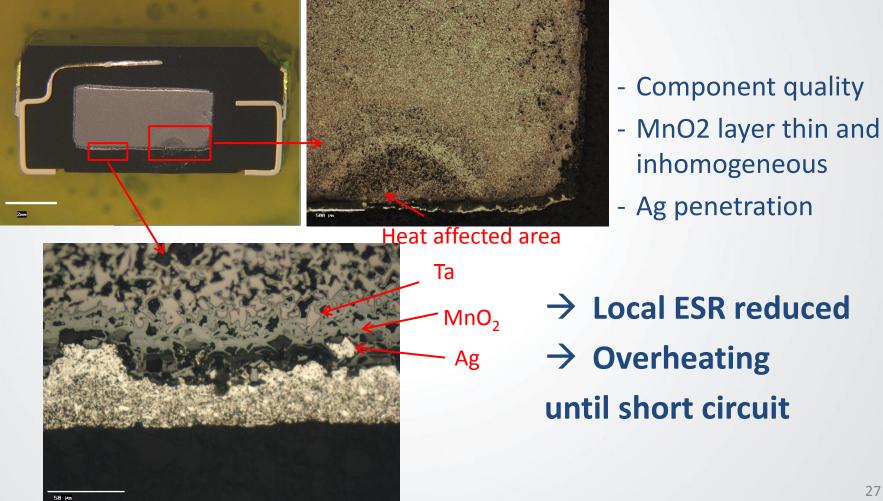


Tantalum Capacitors Main Defects





Tantalum Capacitor MnO2 deposition



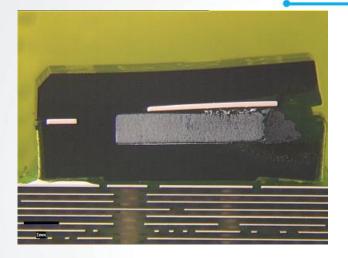


Tantalum Capacitors Main Defects

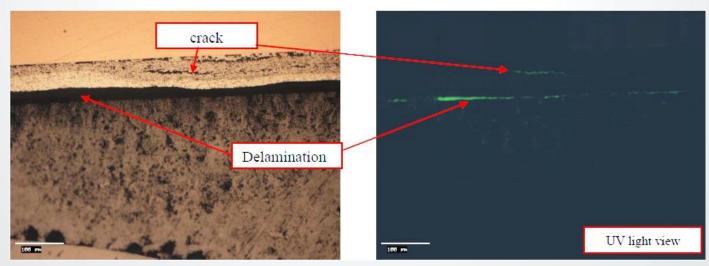


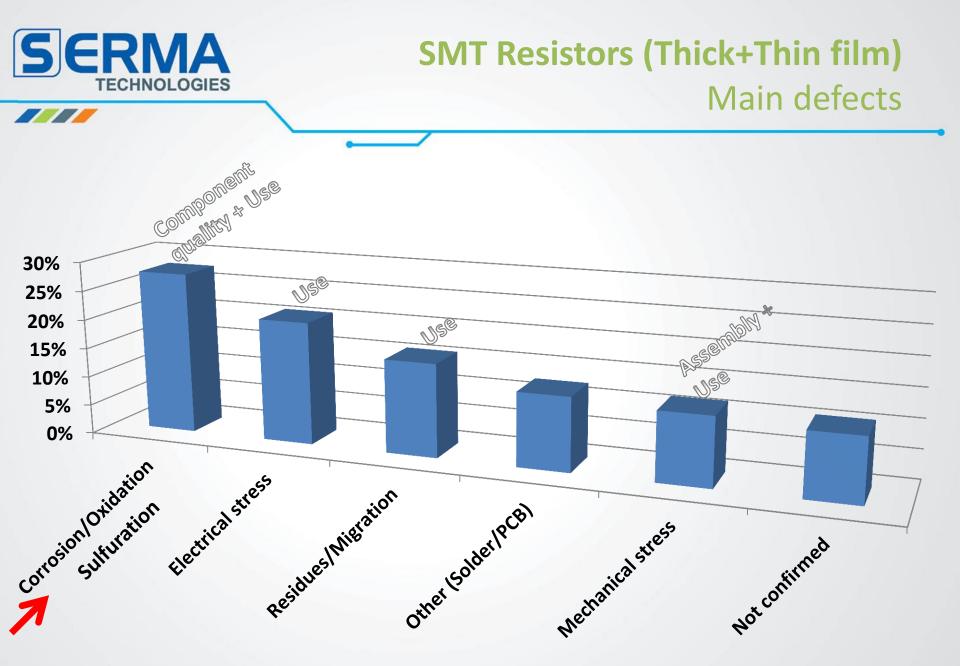


Tantalum Capacitors Delamination



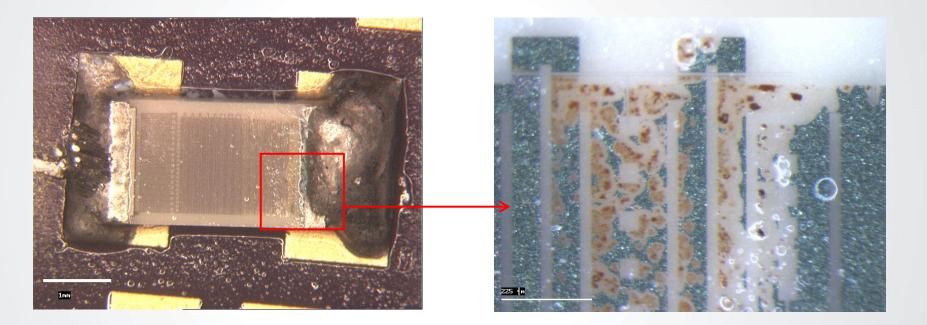
Delamination due to component quality or assembly process → ESR increase up to thermal runaway



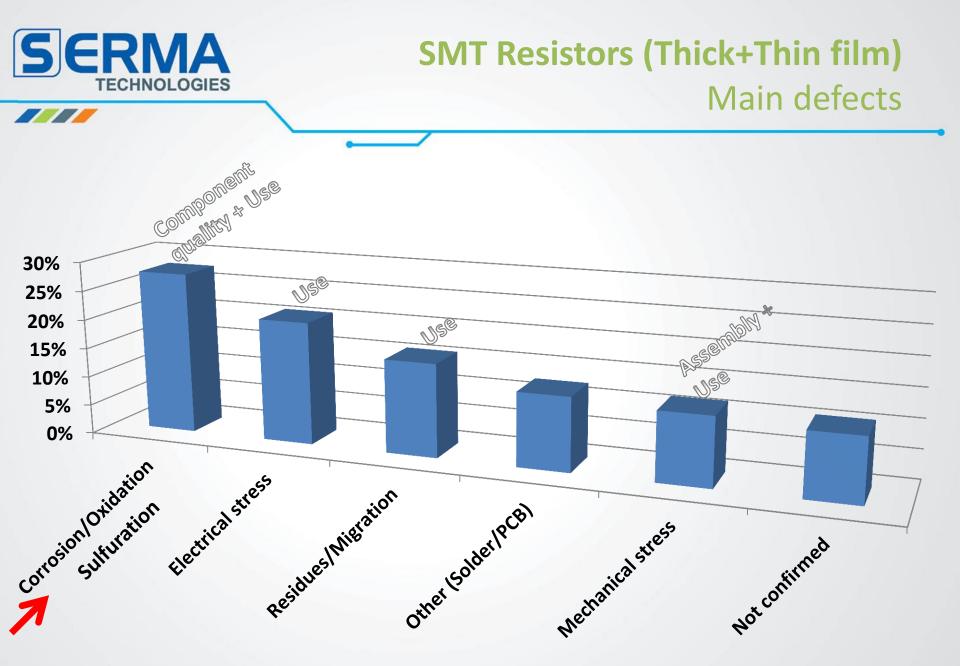




SMT Resistors (Thin film) Corrosion



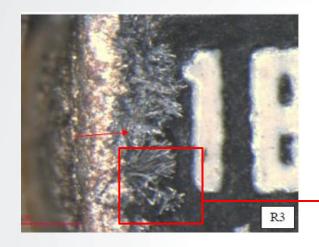
→ Resistance increases up to open circuit

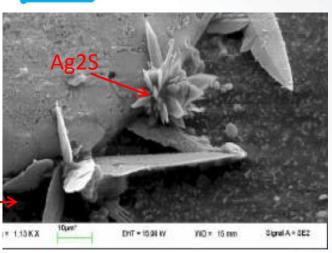


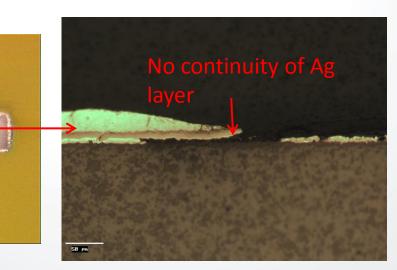


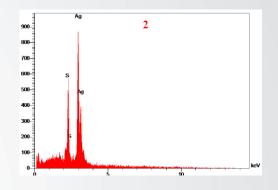
100

SMT Resistors (Thick film) Corrosion (sulfuration)









Environment: Sulfur attack of silver occurs at the interface of the glass passivation layer and the resistor termination → Open circuit

Headquarters in Pessac

Thank you

SERMA TECHNOLOGIES

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